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Vishay Siliconix

AUTOMOTIVE

RoHS

COMPLIANT

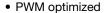
FREE

# Automotive N-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	60			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.023			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.028			
I <sub>D</sub> (A)	18			
Configuration	Single			

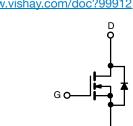
## FEATURES

- TrenchFET® power MOSFET
- Low thermal resistance PowerPAK® 1212-8 package with 1.07 mm profile

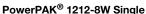


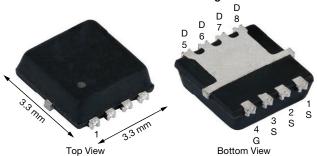
- 100 % R<sub>a</sub> and UIS tested
- AEC-Q101 qualified
- Wettable flank terminals

 Material categorization: for definitions of compliance please see <a href="https://www.vishav.com/doc?99912"><u>www.vishav.com/doc?99912</u></a>



N-Channel MOSFET





Marking Code: Q020

ORDERING INFORMATION	
Package	PowerPAK 1212-8W
Lead (Pb)-free and Halogen-free	SQ7414AENW-T1-GE3

ABSOLUTE MAXIMUM RATINGS ( $T_C = 25$ °C	C, unless otherw	vise noted)			
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		$V_{DS}$	60	V	
Gate-Source Voltage		$V_{GS}$	± 20	v	
Continuous Drain Current <sup>a</sup>	T <sub>C</sub> = 25 °C	- I <sub>D</sub>	18		
Continuous Drain Current "	T <sub>C</sub> = 125 °C		18		
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	18	Α	
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	72		
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	20		
Single Pulse Avalanche Energy	L = 0.1 IIII	E <sub>AS</sub>	16	mJ	
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C	В	62	W	
Maximum Fower dissipation ~	T <sub>C</sub> = 125 °C	$P_{D}$	20	VV	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C	
Soldering Recommendations (Peak Temperature) <sup>d</sup>			260		

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount <sup>c</sup>	$R_{thJA}$	81	°C/W
Junction-to-Case (Drain)		$R_{thJC}$	2.4	C/ VV

#### Notes

- a. Package limited.
- b. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- c. When mounted on 1" square PCB (FR4 material).
- d. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static				L		L	l
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> =	= 0 V, I <sub>D</sub> = 250 μA	60	-	-	V
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	= V <sub>GS</sub> , I <sub>D</sub> = 250 μA	1.5	2	2.5	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	0 V, V <sub>GS</sub> = ± 20 V	-	-	± 100	nA
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 60 V	-	-	1	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 60 V, T <sub>J</sub> = 125 °C	-	-	50	μΑ
		$V_{GS} = 0 V$	V <sub>DS</sub> = 60 V, T <sub>J</sub> = 175 °C	-	-	150	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 \text{ V}$	20	-	-	Α
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 8.7 A	-	0.016	0.023	Ω
Drain-Source On-State Resistance <sup>a</sup>	D	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 8.7 A, T <sub>J</sub> = 125 °C	-	-	0.039	
Drain-Source On-State Resistance "	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 8.7 A, T <sub>J</sub> = 175 °C	-	-	0.050	
		V <sub>GS</sub> = 4.5 V	I <sub>D</sub> = 8.7 A	-	0.019	0.028	
Forward Transconductance <sup>b</sup>	9 <sub>fs</sub>	V <sub>DS</sub> :	= 15 V, I <sub>D</sub> = 8.7 A	-	50	-	S
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>			-	1275	1590	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	$V_{DS} = 30 \text{ V, f} = 1 \text{ MHz}$	-	112	140	pF
Reverse Transfer Capacitance	C <sub>rss</sub>			-	42	52	
Total Gate Charge <sup>c</sup>	Qg			-	19	25	
Gate-Source Charge <sup>c</sup>	$Q_{gs}$	$V_{GS} = 10 \text{ V}$	$V_{DS} = 30 \text{ V}, I_{D} = 8.7 \text{ A}$	-	2.6	-	nC
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			-	3.6	-	
Gate Resistance	Rg		f = 1 MHz	0.6	1.12	1.6	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	8	10	
Rise Time <sup>c</sup>	t <sub>r</sub>		= 30 V, $R_L = 30 \Omega$	-	13	16	ns
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 1 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$		-	22	26	
Fall Time <sup>c</sup>	t <sub>f</sub>			-	15	18	
Source-Drain Diode Ratings and Chara	octeristics b						
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	72	Α
Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> = 8.7 A, V <sub>GS</sub> = 0 V		-	0.8	1.2	V

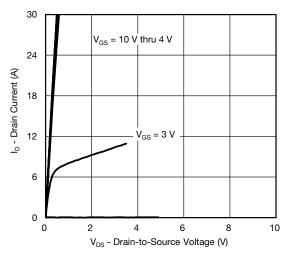
#### Notes

- a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

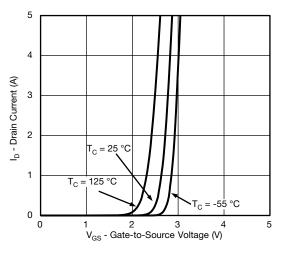
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



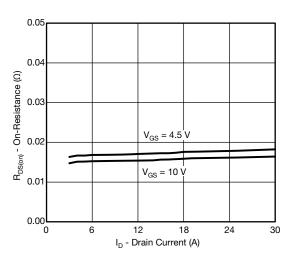
### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



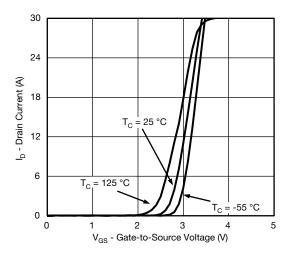
#### **Output Characteristics**



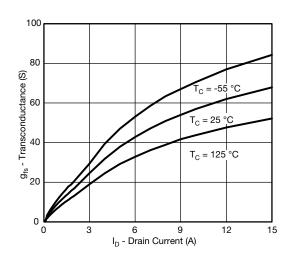
#### **Transfer Characteristics**



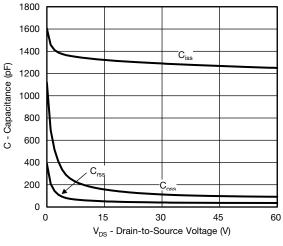
On-Resistance vs. Drain Current



#### **Transfer Characteristics**



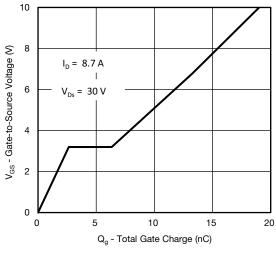
#### Transconductance



Capacitance



### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



# Gate Charge On-Resistance vs. Junction Temperature

2.5

2.1

1.7

1.3

0.9

0.5 **L** -50  $I_D = \dot{8}.7 A$ 

V<sub>GS</sub> = 110 V

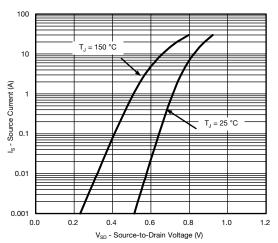
25

75

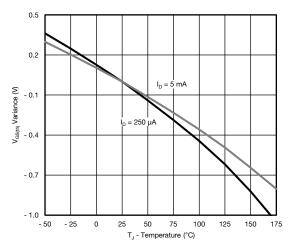
Junction Temperature (°C)

125

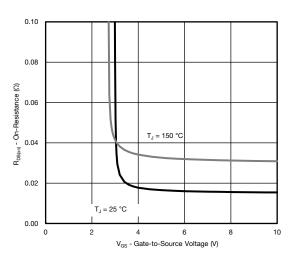
R<sub>DS(on)</sub> - On Resistance (Normalized)



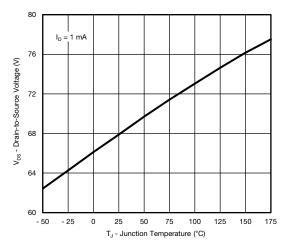




**Threshold Voltage** 



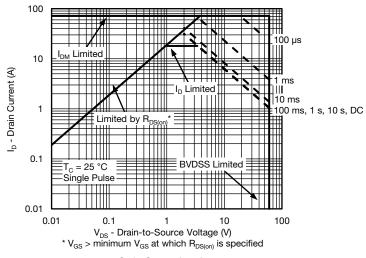
On-Resistance vs. Gate-to-Source Voltage



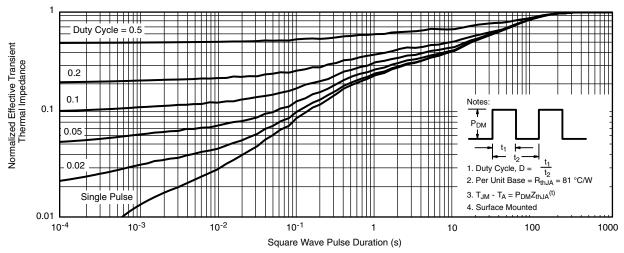
**Drain Source Breakdown vs. Junction Temperature** 



### **THERMAL RATINGS** ( $T_A = 25$ °C, unless otherwise noted)



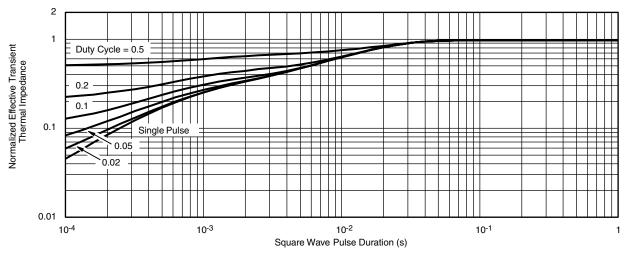
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



### THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

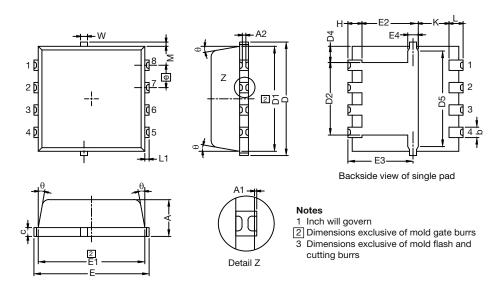
- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?62980.



## PowerPAK® 1212-8W Case Outline



DIM.	MILLIMETERS		INCHES			
DINI.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
Α	0.97	1.04	1.12	0.038	0.041	0.044
A1	0	-	0.05	0	-	0.002
A2	0	-	0.13	0	-	0.005
b	0.23	0.30	0.41	0.009	0.012	0.016
С	0.23	0.28	0.33	0.009	0.011	0.013
D	3.20	3.30	3.40	0.126	0.130	0.134
D1	2.95	3.05	3.15	0.116	0.120	0.124
D2	1.98	2.11	2.24	0.078	0.083	0.088
D4	0.47 typ.			0.0185 typ.		
D5		2.3 typ.			0.090 typ.	
Е	3.20	3.30	3.40	0.126	0.130	0.134
E1	2.95	3.05	3.15	0.116	0.120	0.124
E2	1.47	1.60	1.73	0.058	0.063	0.068
E3	1.75	1.85	1.98	0.069	0.073	0.078
E4		0.34 typ.		0.013 typ.		
е		0.65 BSC.		0.026 BSC		
K		0.86 typ.		0.034 typ.		
Н	0.30	0.41	0.51	0.012	0.016	0.020
L	0.30	0.43	0.56	0.012	0.017	0.022
L1	0.06	0.13	0.20	0.002	0.005	0.008
θ	0°	-	12°	0°	-	12°
W	0.15	0.25	0.36	0.006	0.010	0.014
М		0.125 typ.		0.005 typ.		

DWG: 6032



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